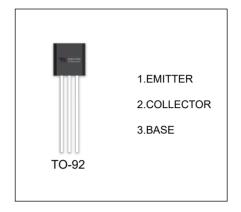


C1815 TRANSISTOR (NPN)

FEATURES Power dissipation



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
C1815	TO-92	Bulk	1000pcs/Bag
C1815-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current -Continuous	150	mA
Pc	Collector Power Dissipation	400	mW
R ₀ JA	Thermal Resistance from Junction to Ambient	312	°C/W
T _{stg}	Operation Junction and Storage Temperature Range	-55 ~+ 150	°C



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100uA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 0. 1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100uA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} = 60V,I _E =0			0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} =5V,I _C =0			0.1	uA
DC current gain	h _{FE}	V _{CE} = 6 V, I _C = 2mA	70		700	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA			0.25	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA			1	V
Transition frequency	f _T	V _{CE} =10 V, I _C = 1mA f=30MHz	80			MHz
Collector Output Capacitance	Cob	V _{CB} =10V,I _E =0 f=1MHz			3.5	pF
Noise Figure	NF	V_{CE} =6V, I_{C} =0.1mA f=1KHz, R_{G} =10K			10	dB

CLASSIFICATION OF hFE

Rank	0	Y	GR	BL
Range	70-140	120-240	200-400	350-700



